

## GaAs HEMT MMIC MEDIUM POWER AMPLIFIER, 37 - 45 GHz

### Typical Applications

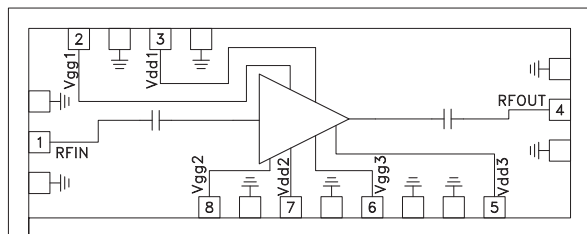
This HMC-APH403 is ideal for:

- Point-to-Point Radios
- Point-to-Multi-Point Radios
- Military & Space

### Features

Output IP3: +32 dBm  
P1dB: +23 dBm  
Gain: 21 dB  
Supply Voltage: +5V  
50 Ohm Matched Input/Output  
Die Size: 2.76 x 1.03 x 0.1 mm

### Functional Diagram



### General Description

The HMC-APH403 is a three stage GaAs HEMT MMIC Medium Power Amplifier which operates between 37 and 45 GHz. The HMC-APH403 provides 21 dB of gain, and an output power of +23 dBm at 1 dB compression from a +5 V supply voltage. All bond pads and the die backside are Ti/Au metallized and the amplifier device is fully passivated for reliable operation. The HMC-APH403 GaAs HEMT MMIC Medium Power Amplifier is compatible with conventional die attach methods, as well as thermocompression and thermosonic wire bonding, making it ideal for MCM and hybrid microcircuit applications. All data Shown herein is measured with the chip in a 50 Ohm environment and contacted with RF probes.

### Electrical Specifications <sup>[1]</sup>, $T_A = +25^\circ \text{C}$ , $V_{dd1}=V_{dd2}=V_{dd3}= 5\text{V}$ $I_{dd1}+ I_{dd2} + I_{dd3}= 475 \text{ mA}$ <sup>[2]</sup>

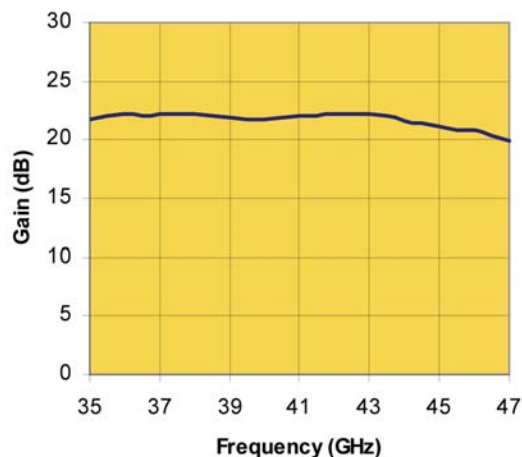
Parameter	Min	Typ	Max	Units
Frequency Range	37 - 45			GHz
Gain	19	21		dB
Input Return Loss		6		dB
Output Return Loss		7		dB
Output Power for 1 dB Compression (P1dB)	22	23		dBm
Output Third Order Intercept (IP3)		32		dBm
Supply Current ( $I_{dd1} + I_{dd2} + I_{dd3}$ )		475		dBm

[1] Unless otherwise indicated, all measurements are from probed die

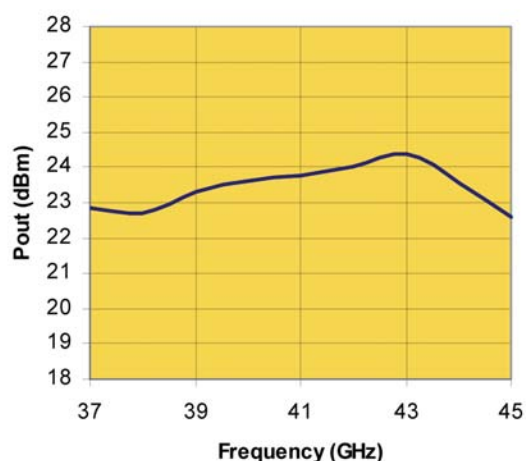
[2] Adjust  $V_{gg1}=V_{gg2}=V_{gg3}$  between -1V to +0.3V (typ -0.5V).

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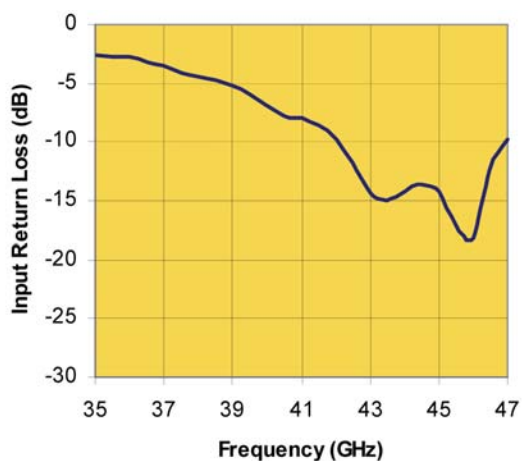
**Pulsed Gain vs. Frequency**



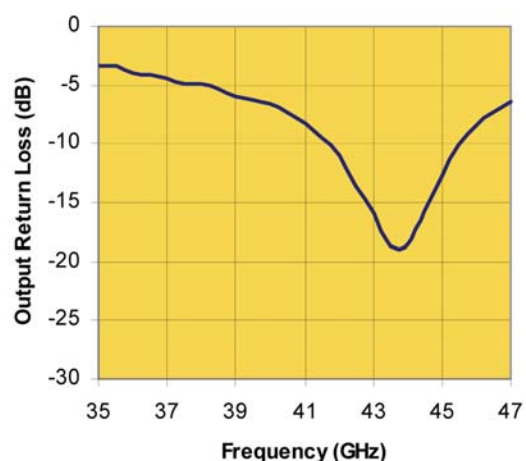
**Fixtured P1dB vs. Frequency**



**Input Return Loss vs. Frequency**



**Output Return Loss vs. Frequency**



Note: Measured Performance Characteristics (Typical Performance at 25°C) Vdd = 5V, Idd = 475 mA

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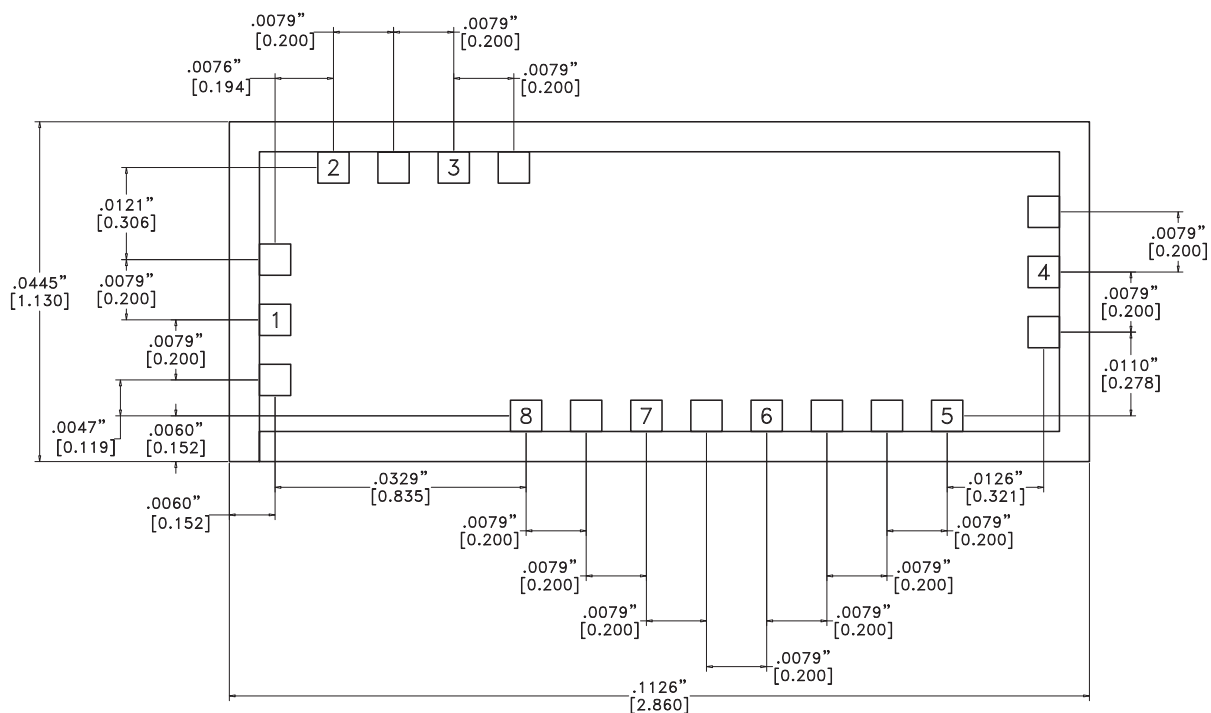
### Absolute Maximum Ratings

Drain Bias Voltage	+5.5 Vdc
Gate Bias Voltage	-1 to +0.3 Vdc
RF Input Power	10 dBm
Thermal Resistance (Channel to die bottom)	49.7 °C/W
Storage Temperature	-65 °C to + 125 °C



ELECTROSTATIC SENSITIVE DEVICE  
OBSERVE HANDLING PRECAUTIONS

### Outline Drawing



#### NOTES:

1. ALL DIMENSIONS ARE IN INCHES [MM].
2. TYPICAL BOND PAD IS .004" SQUARE.
3. BACKSIDE METALLIZATION: GOLD.
4. BACKSIDE METAL IS GROUND.
5. BOND PAD METALLIZATION: GOLD.
6. CONNECTION NOT REQUIRED FOR UNLABELED BOND PADS.
7. OVERALL DIE SIZE  $\pm .002$ "